

# Dual Series Switching Diodes

## Features

- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.
- The LBAV99WT1G is a smaller package, equivalent to the LBAV99LT1G.

## Suggested Applications

- ESD Protection
- Polarity Reversal Protection
- Data Line Protection
- Inductive Load Protection
- Steering Logic

## ORDERING INFORMATION

Device	Package	Shipping
LBAV99WT1G	SOT-323(SC-70)	3000/Tape & Reel
S-LBAV99WT1G		
LBAV99RWT1G	SOT-323(SC-70)	3000/Tape & Reel
S-LBAV99RWT1G		
LBAV99WT3G	SOT-323(SC-70)	10000/Tape & Reel
S-LBAV99WT3G		
LBAV99RWT3G	SOT-323(SC-70)	10000/Tape & Reel
S-LBAV99RWT3G		

## DEVICE MARKING

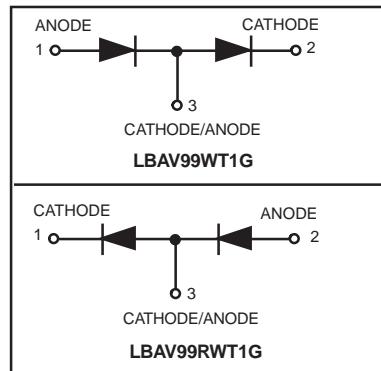
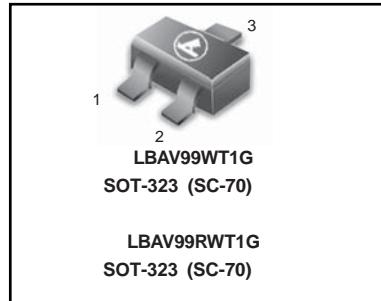
LBAV99WT1G = A7; LBAV99RWT1G = F7

## MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	70	Vdc
Forward Current	$I_F$	215	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Repetitive Peak Reverse Voltage	$V_{RRM}$	70	V
Average Rectified Forward Current (Note 1.) (averaged over any 20 ms period)	$I_{F(AV)}$	715	mA
Repetitive Peak Forward Current	$I_{FRM}$	450	mA
Non-Repetitive Peak Forward Current	$I_{FSM}$		A
$t = 1.0 \mu s$		2.0	
$t = 1.0 \text{ ms}$		1.0	
$t = 1.0 \text{ S}$		0.5	

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

**LBAV99WT1G  
S-LBAV99WT1G  
LBAV99RWT1G  
S-LBAV99RWT1G**



# **LBAV99WT1G, S-LBAV99WT1G LBAV99RWT1G, S-LBAV99RWT1G**

## **THERMAL CHARACTERISTICS**

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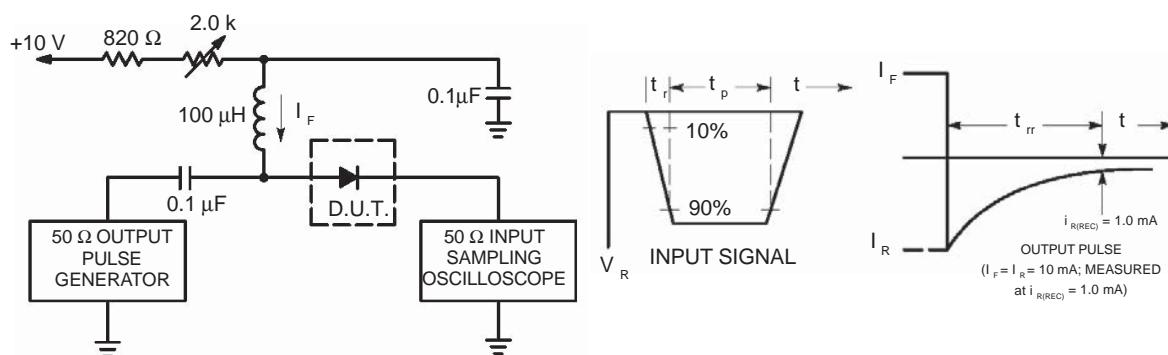
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1.) $T_A = 25^\circ\text{C}$	$P_D$	200	mW
Derate above $25^\circ\text{C}$		1.6	$\text{mW}/^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta,JA}$	625	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2.) $T_A = 25^\circ\text{C}$	$P_D$	300	mW
Derate above $25^\circ\text{C}$		2.4	$\text{mW}/^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta,JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

## **ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Each Diode)**

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Reverse Breakdown Voltage ( $I_{(BR)} = 100 \mu\text{A}$ )	$V_{(BR)}$	70	—	Vdc
Reverse Voltage Leakage Current ( $V_R = 70 \text{ Vdc}$ )	$I_R$	—	2.5	$\mu\text{Adc}$
( $V_R = 25 \text{ Vdc}, T_J = 150^\circ\text{C}$ )		—	30	
( $V_R = 70 \text{ Vdc}, T_J = 150^\circ\text{C}$ )		—	50	
Diode Capacitance ( $V_R = 0, f = 1.0 \text{ MHz}$ )	$C_D$	—	1.5	pF
Forward Voltage ( $I_F = 1.0 \text{ mAdc}$ )	$V_F$	—	715	mVdc
( $I_F = 10 \text{ mAdc}$ )		—	855	
( $I_F = 50 \text{ mAdc}$ )		—	1000	
( $I_F = 150 \text{ mAdc}$ )		—	1250	
Reverse Recovery Time $R_L = 100 \Omega$ ( $I_F = I_R = 10 \text{ mA}, i_{R(\text{REC})} = 1.0 \text{ mA}$ ) (Figure 1)	$t_{rr}$	—	6.0	ns
Forward Recovery Voltage ( $I_F = 10 \text{ mA}, t_r = 20 \text{ ns}$ )	$V_{FR}$	—	1.75	V

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



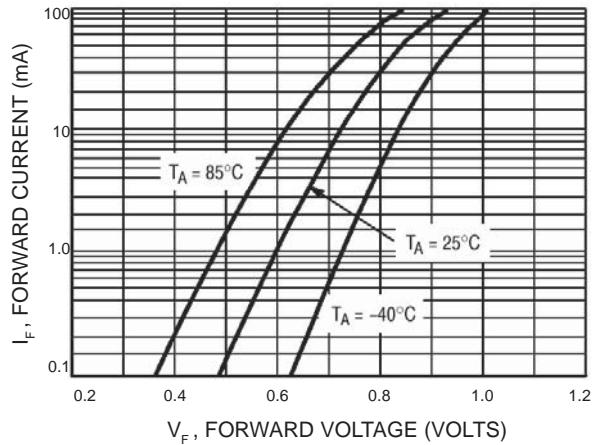
Notes: 1. A  $2.0 \text{ k}\Omega$  variable resistor adjusted for a Forward Current ( $I_F$ ) of  $10\text{mA}$ .

2. Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to  $10\text{mA}$ .

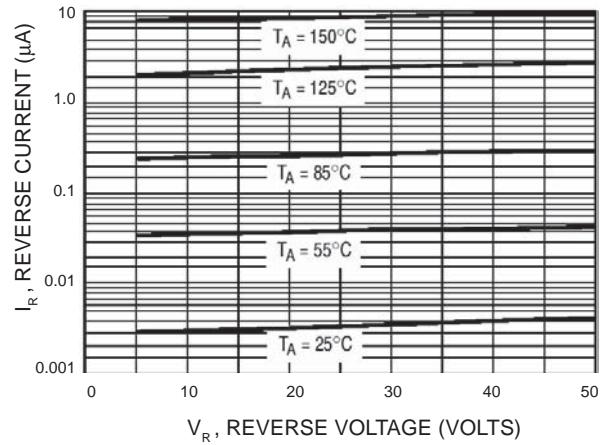
3.  $t_p \gg t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

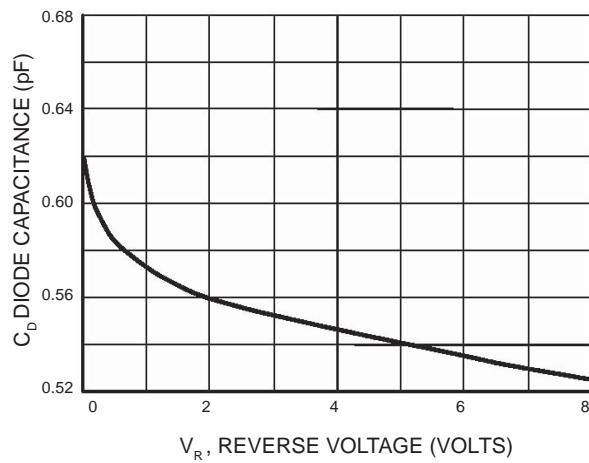
# LBAV99WT1G, S-LBAV99WT1G LBAV99RWT1G, S-LBAV99RWT1G



**Figure 2. Forward Voltage**



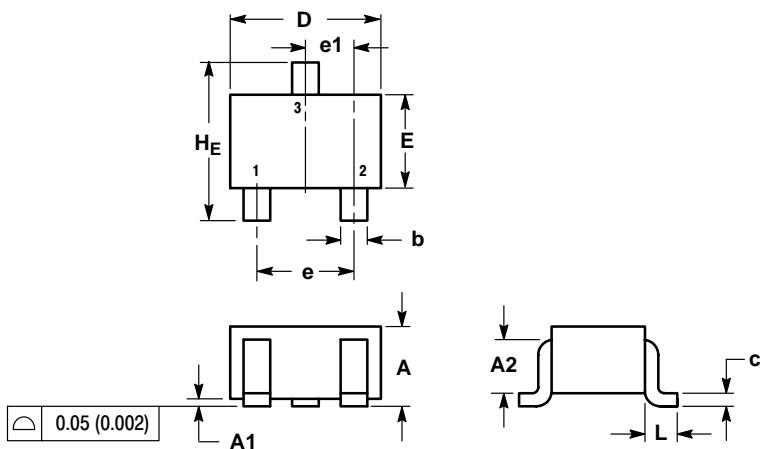
**Figure 3. Leakage Current**



**Figure 4. Capacitance**

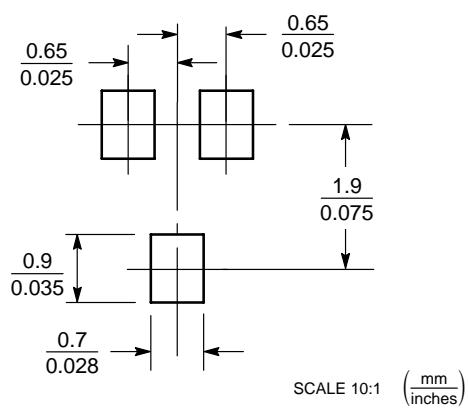
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**SC-70 (SOT-323)**



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.7 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.425 REF			0.017 REF		
H_E	2.00	2.10	2.40	0.079	0.083	0.095

### SOLDERING FOOTPRINT\*



SCALE 10:1  $(\frac{\text{mm}}{\text{inches}})$

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